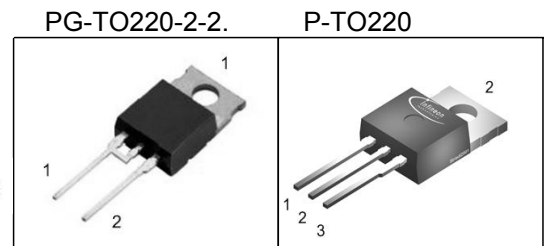


Silicon Carbide Schottky Diode

- Revolutionary semiconductor material - Silicon Carbide
- Switching behavior benchmark
- No reverse recovery
- No temperature influence on the switching behavior
- No forward recovery
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC⁰⁾ for target applications

thinQ!™ SiC Schottky Diode
Product Summary

V_{RRM}	300	V
Q_C	23	nC
I_F	10	A



Type	Package	Ordering Code	Marking	Pin 1	Pin 2	Pin 3
SDP10S30	P-TO220-3	Q67040-S4372	D10S30	n.c.	C	A
SDT10S30	PG-TO220-2-2.	Q67040-S4447	D10S30	C	A	

Maximum Ratings, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous forward current, $T_C=100^\circ\text{C}$	I_F	10	A
RMS forward current, $f=50\text{Hz}$	I_{FRMS}	14	
Surge non repetitive forward current, sine halfwave $T_C=25^\circ\text{C}$, $t_p=10\text{ms}$	I_{FSM}	36	
Repetitive peak forward current $T_j=150^\circ\text{C}$, $T_C=100^\circ\text{C}$, $D=0.1$	I_{FRM}	45	
Non repetitive peak forward current $t_p=10\mu\text{s}$, $T_C=25^\circ\text{C}$	I_{FMAX}	100	
i^2t value, $T_C=25^\circ\text{C}$, $t_p=10\text{ms}$	$\int i^2 dt$	6.5	A ² s
Repetitive peak reverse voltage	V_{RRM}	300	V
Surge peak reverse voltage	V_{RSM}	300	
Power dissipation, $T_C=25^\circ\text{C}$	P_{tot}	65	W
Operating and storage temperature	T_j, T_{stg}	-55... +175	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Thermal resistance, junction - case	R_{thJC}	-	-	2.3	K/W

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Diode forward voltage	V_F				V
$I_F=10\text{A}, T_j=25^\circ\text{C}$		-	1.5	1.7	
$I_F=10\text{A}, T_j=150^\circ\text{C}$		-	1.5	1.9	
Reverse current	I_R				μA
$V_R=300\text{V}, T_j=25^\circ\text{C}$		-	15	200	
$V_R=300\text{V}, T_j=150^\circ\text{C}$		-	20	1000	

⁰J-STD20 and JESD22

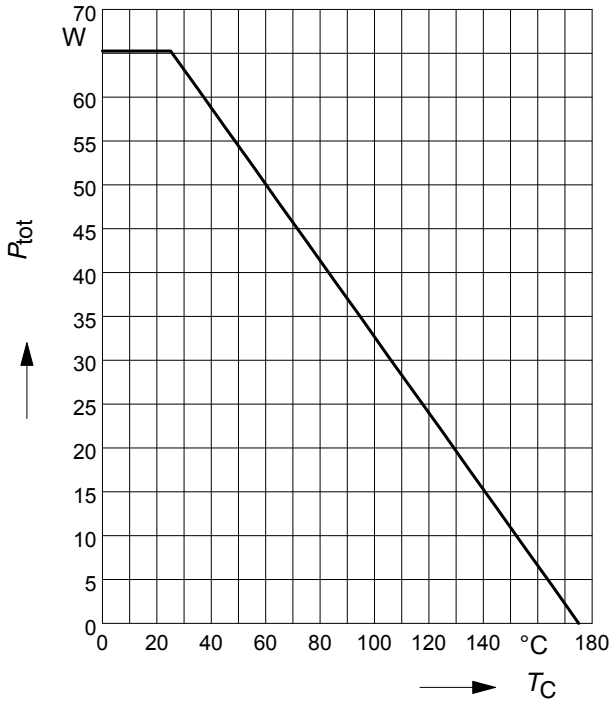
¹Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air.

Electrical Characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics					
Total capacitive charge ¹⁾ $V_R=200\text{V}$, $I_F=10\text{A}$, $di_F/dt=-200\text{A}/\mu\text{s}$, $T_j=150\text{°C}$	Q_C	-	23	-	nC
Switching time ²⁾ $V_R=200\text{V}$, $I_F=10\text{A}$, $di_F/dt=-200\text{A}/\mu\text{s}$, $T_j=150\text{°C}$	t_{rr}	-	n.a.	-	ns
Total capacitance $V_R=0\text{V}$, $T_C=25\text{°C}$, $f=1\text{MHz}$ $V_R=150\text{V}$, $T_C=25\text{°C}$, $f=1\text{MHz}$ $V_R=300\text{V}$, $T_C=25\text{°C}$, $f=1\text{MHz}$	C	-	600 55 40	-	pF

1 Power dissipation

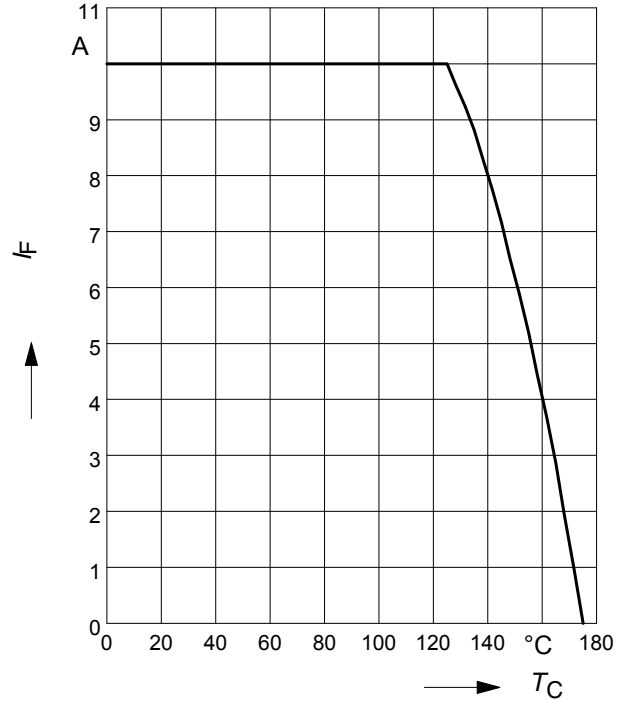
$$P_{\text{tot}} = f(T_C)$$



2 Diode forward current

$$I_F = f(T_C)$$

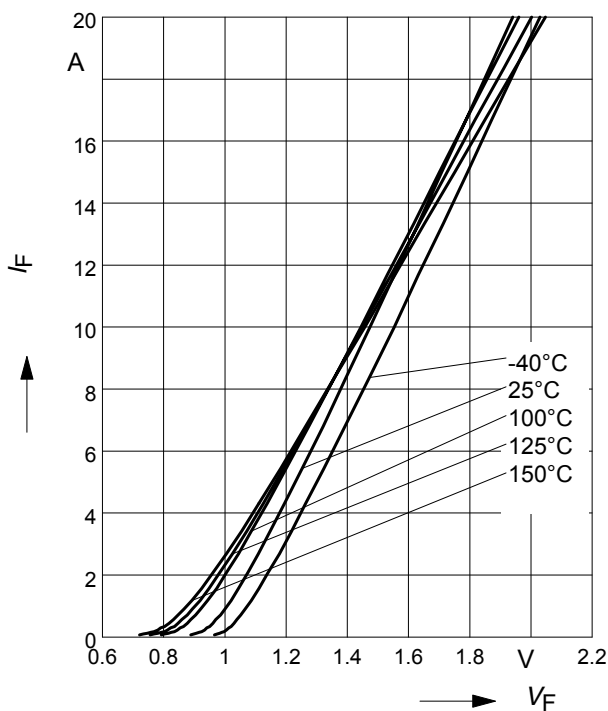
parameter: $T_j \leq 175^\circ\text{C}$



3 Typ. forward characteristic

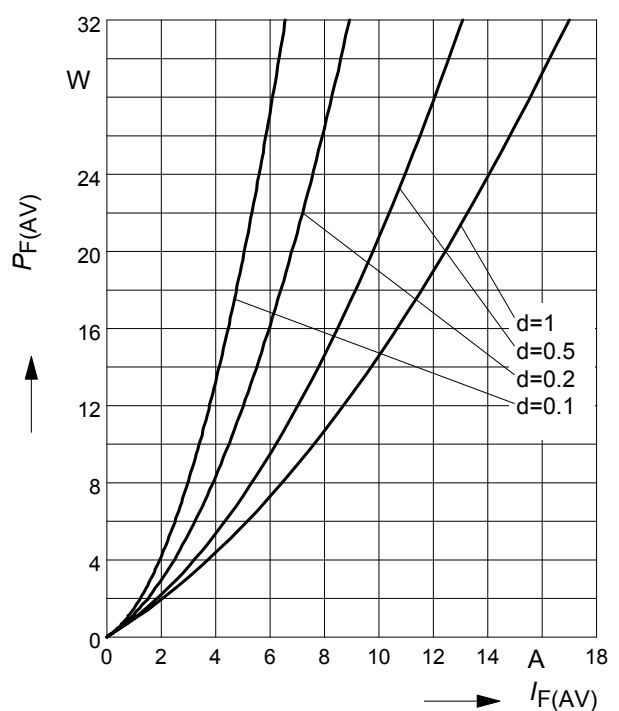
$$I_F = f(V_F)$$

parameter: T_j , $t_p = 350 \mu\text{s}$



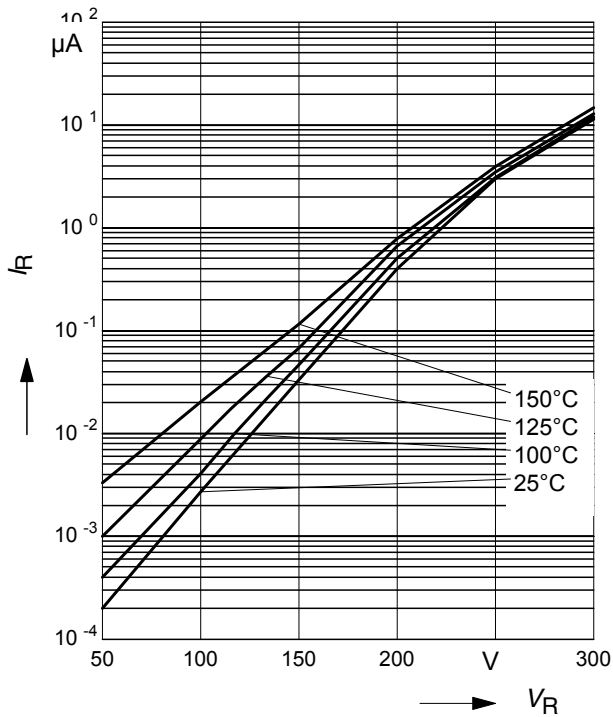
4 Typ. forward power dissipation vs. average forward current

$$P_{F(\text{AV})} = f(I_F) \quad T_C = 100^\circ\text{C}, d = t_p/T$$



5 Typ. reverse current vs. reverse voltage

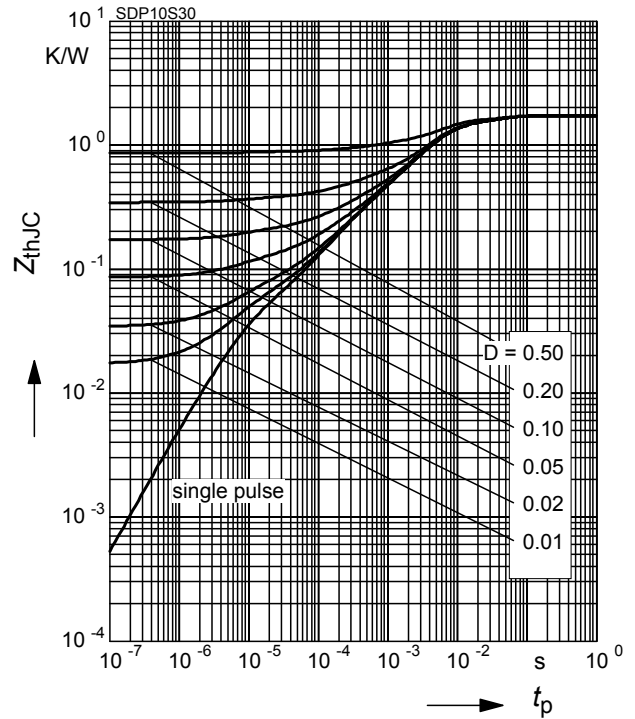
$$I_R = f(V_R)$$



6 Transient thermal impedance

$$Z_{thJC} = f(t_p)$$

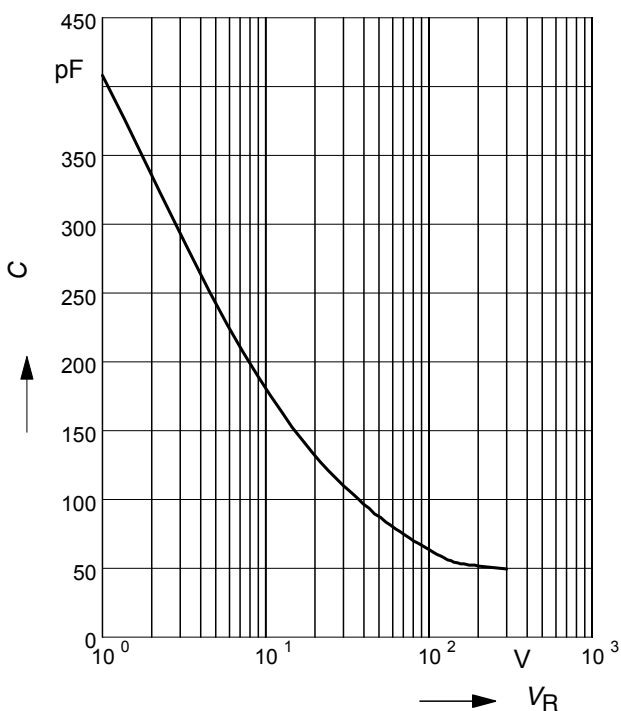
parameter : $D = t_p/T$



7 Typ. capacitance vs. reverse voltage

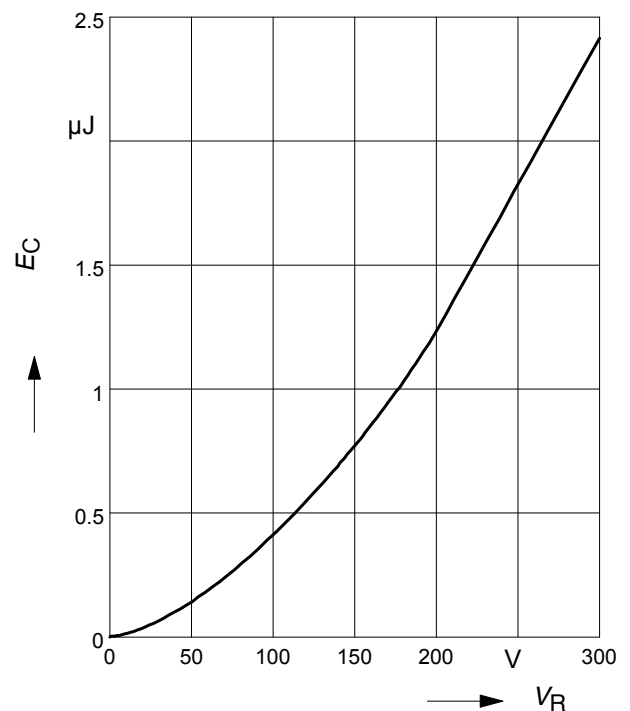
$$C = f(V_R)$$

parameter: $T_C = 25\text{ °C}$, $f = 1\text{ MHz}$



8 Typ. C stored energy

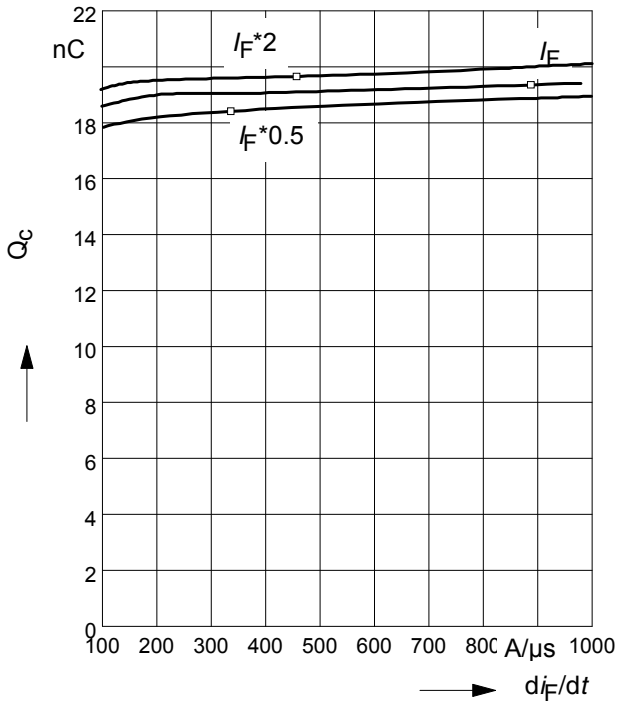
$$E_C = f(V_R)$$



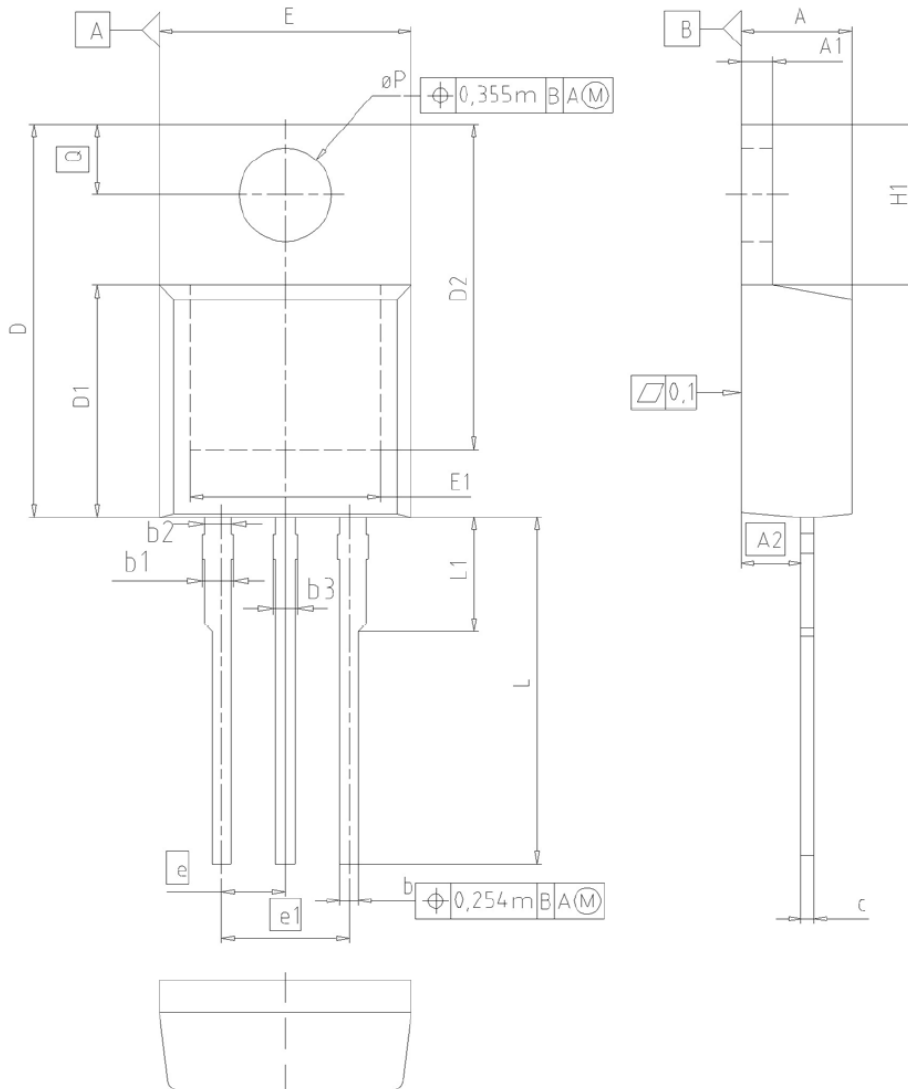
9 Typ. capacitive charge vs. current slope

$$Q_C = f(di_F/dt)$$

parameter: $T_j = 150\text{ }^\circ\text{C}$



P-TO220-3-1, P-TO220-3-21



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.57	0.169	0.180
A1	1.17	1.40	0.046	0.055
A2	2.15	2.72	0.085	0.107
b	0.65	0.86	0.026	0.034
b1	0.95	1.40	0.037	0.055
b2	0.95	1.15	0.037	0.045
b3	0.65	1.15	0.026	0.045
c	0.33	0.60	0.013	0.024
D	14.81	15.95	0.583	0.628
D1	8.51	9.45	0.335	0.372
D2	12.19	13.10	0.480	0.516
E	9.70	10.36	0.382	0.408
E1	6.50	8.60	0.256	0.339
e	2.54		0.100	
e1	5.08		0.200	
N	3		3	
H1	5.90	6.90	0.232	0.272
L	13.00	14.00	0.512	0.551
L1	-	4.80	-	0.189
øP	3.60	3.89	0.142	0.153
Q	2.60	3.00	0.102	0.118

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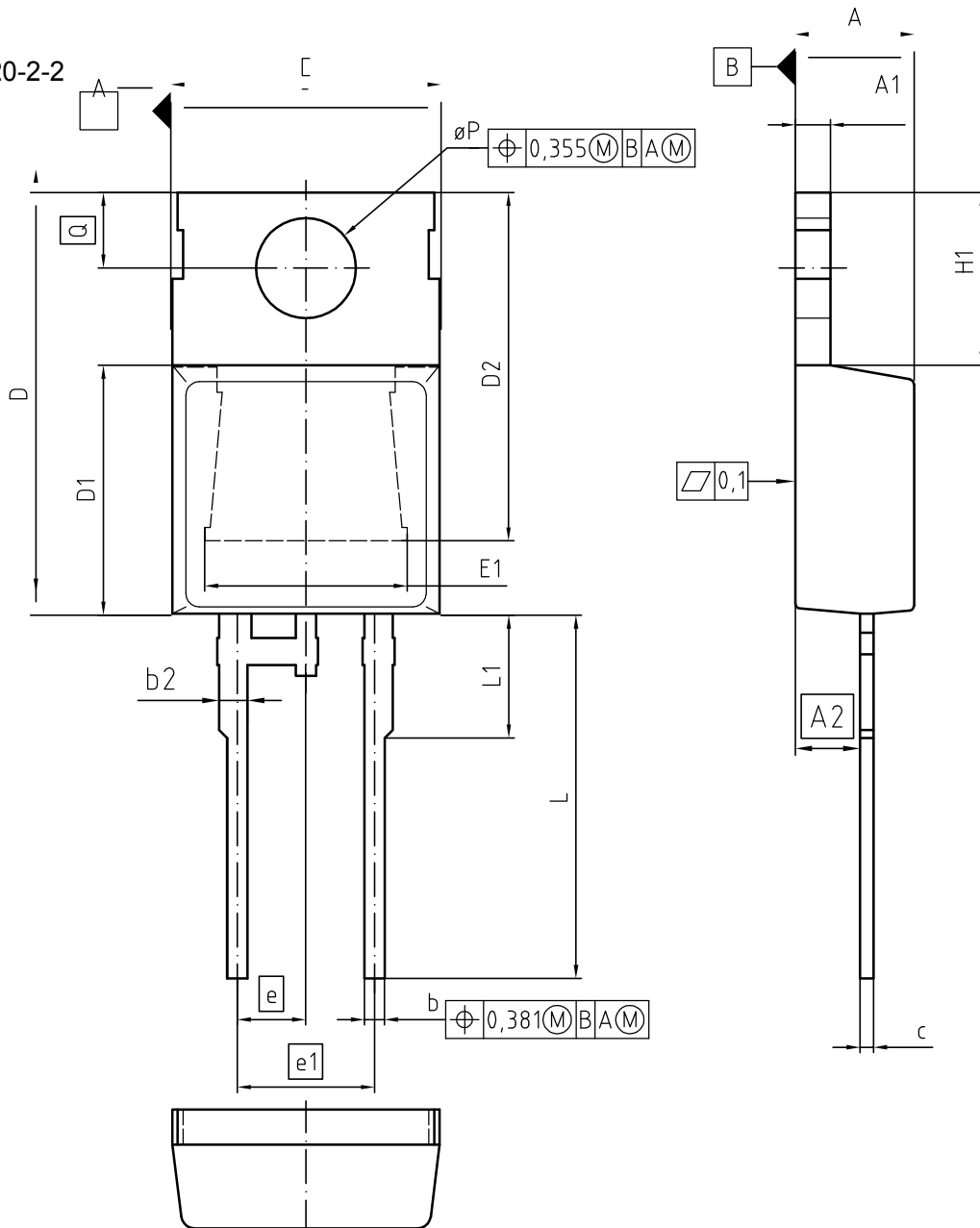
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PG-TO-220-2-2



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.191	4.699	0.165	0.185
A1	1.170	1.400	0.046	0.055
b2	2.215	2.718	0.087	0.107
b	0.635	0.889	0.025	0.035
ϕ	0.950	1.651	0.037	0.065
D	0.330	0.635	0.013	0.025
D1	14.808	15.950	0.583	0.628
D2	8.509	9.450	0.335	0.372
E1	12.850	14.245	0.506	0.561
E	9.677	10.363	0.381	0.408
e1	6.500	8.788	0.256	0.346
e	2.540		0.100	
N	5.080		0.200	
H	2		2	
L1	5.900	6.900	0.232	0.272
L	12.700	14.000	0.500	0.551
$\phi 1$	3.048	4.800	0.120	0.189
ϕP	3.550	3.886	0.140	0.153
L	2.540	3.048	0.100	0.120

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